

## IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): An aqueous dispersion for chemical mechanical polishing obtained by mixing a water-soluble quaternary ammonium salt, an inorganic acid salt and abrasive grains into an aqueous medium, and is used in polishing of a silicon type film including a polysilicon film and/or amorphous silicon film.

Claim 2 (Original): The aqueous dispersion for chemical mechanical polishing according to claim 1, wherein the water-soluble quaternary ammonium salt, inorganic acid salt and abrasive grains are contained in proportions of 0.005 to 5 % by mass, 0.005 to 5 % by mass and 0.01 to 10 % by mass, respectively.

Claim 3 (Original): The aqueous dispersion for chemical mechanical polishing according to claim 1, which further comprises a water-soluble polymer.

Claim 4 (Original): The aqueous dispersion for chemical mechanical polishing according to claim 1, wherein the water-soluble quaternary ammonium salt is a compound represented by the following formula (1):



wherein R is an alkyl group having 1 to 4 carbon atoms.

Claim 5 (Original): The aqueous dispersion for chemical mechanical polishing according to claim 1, wherein the inorganic acid salt is an inorganic ammonium salt.

Claim 6 (Canceled).

Claim 7 (Currently Amended): A chemical mechanical polishing process comprising a step of polishing a surface to be polished formed of at least a polysilicon film and/or amorphous silicon film, with the aqueous dispersion for chemical mechanical polishing according to claim 1.

Claim 8 (Original): The chemical mechanical polishing process according to claim 7, wherein a first specific removal rate ratio represented by a ratio of the removal rate of a polysilicon film to the removal rate of a silicon oxide film in the case where the silicon oxide film and the polysilicon film are polished under the same condition, is at least 30.

Claim 9 (Original): The chemical mechanical polishing process according to claim 7, wherein a second specific removal rate ratio represented by a ratio of the removal rate of a polysilicon film to the removal rate of a nitride film in the case where the nitride film and the polysilicon film are polished under the same condition, is at least 50.

Claim 10 (Currently Amended): A process for producing a semiconductor device, wherein the semiconductor device is produced by conducting step of polishing a surface to be polished formed of at least a polysilicon film and/or amorphous silicon film on a semiconductor substrate, with the aqueous dispersion for chemical mechanical polishing according to claim 1.

Claim 11 (Currently Amended): An aqueous dispersion for chemical mechanical polishing obtained by mixing at least a water-soluble quaternary ammonium salt, another

basic organic compound than the water-soluble quaternary ammonium salt, an inorganic acid salt, a water-soluble polymer and abrasive grains into an aqueous medium, and is used in polishing of a silicon type film including a polysilicon film and/or amorphous silicon film.

Claim 12 (Original): The aqueous dispersion for chemical mechanical polishing according to claim 11 wherein the water-soluble quaternary ammonium salt, another basic organic compound than the water-soluble quaternary ammonium salt, inorganic acid salt, water-soluble polymer and abrasive grains are contained in proportions of 0.005 to 10 % by mass, 0.005 to 10 % by mass, 0.005 to 8 % by mass, 0.001 to 5 % by mass and 0.01 to 10 % by mass, respectively.

Claim 13 (Original): The aqueous dispersion for chemical mechanical polishing according to claim 11, wherein the water-soluble quaternary ammonium salt is a compound represented by the following formula (1):



wherein R is an alkyl group having 1 to 4 carbon atoms.

Claim 14 (Original): The aqueous dispersion for chemical mechanical polishing according to claim 11, wherein the inorganic acid salt is an inorganic ammonium salt.

Claim 15 (Canceled).

Claim 16 (Currently Amended): A chemical mechanical polishing process comprising a step of polishing a surface to be polished formed of at least a polysilicon film

and/or amorphous silicon film, with the aqueous dispersion for chemical mechanical polishing according to claim 11.

Claim 17 (Original): The chemical mechanical polishing process according to claim 16, wherein a first specific removal rate ratio represented by a ratio of the removal rate of a polysilicon film to the removal rate of a silicon oxide film in the case where the silicon oxide film and the polysilicon film are polished under the same condition, is at least 30.

Claim 18 (Original): The chemical mechanical polishing process according to claim 16, wherein a second specific removal rate ratio represented by a ratio of the removal rate of a polysilicon film to the removal rate of a nitride film in the case where the nitride film and the polysilicon film are polished under the same condition, is at least 50.

Claim 19 (Currently Amended): A process for producing a semiconductor device, wherein the semiconductor device is produced by conducting a step of polishing a surface to be polished formed of at least a polysilicon film and/or amorphous silicon film on a semiconductor substrate, with the aqueous dispersion for chemical mechanical polishing according to claim 11.

Claim 20 (Currently Amended): A material for preparing an aqueous dispersion for chemical mechanical polishing used in polishing of a silicon type film including a polysilicon film and/or amorphous silicon film, comprising a first aqueous dispersion material (I) obtained by mixing at least a water-soluble quaternary ammonium salt and an inorganic acid salt into an aqueous medium, and a second aqueous dispersion material (II) obtained by mixing at least a water-soluble polymer and another basic organic compound than the water-

soluble quaternary ammonium salt into an aqueous medium, wherein abrasive grains are mixed into at least one of the first aqueous dispersion material (I) and the second aqueous dispersion material (II), and the aqueous dispersion for chemical mechanical polishing is prepared by both of the first aqueous dispersion material (I) and the second aqueous dispersion material (II).

Claim 21 (Original): The material for preparing an aqueous dispersion for chemical mechanical polishing according to claim 20, wherein the water-soluble quaternary ammonium salt is a compound represented by the following formula (1):



wherein R is an alkyl group having 1 to 4 carbon atoms.

Claim 22 (Original): The material for preparing an aqueous dispersion for chemical mechanical polishing according to claim 20, wherein the ratio [(I)/(II)] of the first aqueous dispersion material (I) to the second aqueous dispersion material (II) is 30/70 to 70/30 in terms of a mass ratio.

Claim 23 (Original): The material for preparing an aqueous dispersion for chemical mechanical polishing according to claim 20, wherein the inorganic acid salt is an inorganic ammonium salt.

### DISCUSSION OF THE AMENDMENT

Claims 1, 7, 10, 11 16, 19 and 20 have been amended by reference to polishing of a silicon type film including a polysilicon film and/or amorphous silicon film, as supported in the specification at page 42, lines 2-3 and lines 13-18. Claims 6 and 15 have been canceled.

No new matter is believed to have been added by the above amendment. Claims 1-5, 7-14 and 16-23 are now pending in the application.